Attorney Docket: 0630-1951P Divisional of Application No. 09/863,452

## ABSTRACT OF THE DISCLOSURE

A high voltage device prevents or minimizes the lowering of a maximum operating voltage range. Bulk resistances of the drift regions are reduced by forming trenches within the drift regions and filling the trenches with conductive polysilicon layers. The polysilicon layers reduce the bulk resistances and prevents or minimizes the operation of parasitic bipolar junction transistors typically formed when the high voltage device is manufactured.